TOSHIBA INFRARED LED GaA&As INFRARED EMITTER

T L N 2 0 1

INFRARED LED FOR PHOTOSENSORS

OPTO-ELECTRONIC SWITCHES TAPE AND CARD READERS SMOKE SENSORS EQUIPMENT USING INFRARED TRANSMISSION

- TO-18 metal package.
- High radiant power : $P_0 = 5 \text{ mW} (\text{typ.})$
- High radiant intensity : $I_E = 35 \text{ mW} / \text{sr}(\text{typ.})$
- Excellent radiant-intensity linearity. Modulation by pulse operation and high frequency is possible.
- Highly reliable due to hermetic seal
- Same external shape as TPS708 photodiode

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MAXIMUM RATINGS (Ta = 25^{\circ}C)
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CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	$I_{\mathbf{F}}$	100	mA
Forward Current Derating $(Ta > 25^{\circ}C)$	⊿I _F /°C	-1	mA/°C
Pulse Forward Current (Note)	IFP	1	A
Reverse Voltage	VR	5	V
Operating Temperature Range	T _{opr}	-40~125	°C
Storage Temperature Range	T_{stg}	$-55 \sim 150$	°C



Weight : 0.33 g (typ.)

PIN CONNECTION



- 1. Cathode
- 2. Anode (case)

(Note) : Pulse width $\leq 100~\mu \text{s},$ repetitive frequency = 100 Hz

MARKINGS



Unit : mm

CHARACTERISTIC	SYMBOL	TEST CONDITION	Min	Тур.	Max	UNIT
Forward Voltage	VF	$I_F = 50 \text{ mA}$		1.5	1.9	V
Pulse Forward Voltage	V _{FP}	$I_{FP} = 1 A$	—	5.0	_	V
Reverse Current	IR	$V_R = 5 V$	—	—	10	μA
Radiant Intensity	IE	$I_F = 50 \text{ mA}$	20	35	_	mW/sr
Radiant Power	PO	$I_F = 50 \text{ mA}$	—	5		mW
Capacitance	C_{T}	$V_{R} = 0$, $f = 1 \text{ MHz}$		17		pF
Peak Emission Wavelength	$\lambda_{\mathbf{P}}$	$I_F = 50 \text{ mA}$		880		nm
Spectral Line Half Width	Δλ	$I_F = 50 \text{ mA}$	—	80	_	nm
Half Value Angle	$\theta_{\frac{1}{2}}$	$I_F = 50 \text{ mA}$	_	±7		0

OPTICAL AND ELECTRICAL CHARACTERISTICS ($Ta = 25^{\circ}C$)

PRECAUTIONS

Please be careful of the followings.

- Soldering temperature : 260°C max Soldering time : 5 s max (Soldering must be performed 1.5 m from the bottom of the package.)
- 2. When forming the leads, bend each lead under the 2 mm from the body of the device. Soldering must be performed after the leads have been formed.
- 3. Radiant intensity falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in radiant power over time. The ratio of fluctuation in radiation intensity to fluctuation in optical output is 1:1.

$$\frac{I_{E}(t)}{I_{E}(0)} = \frac{P_{O}(t)}{P_{O}(0)}$$

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